

150V N-Channel Depletion-Mode Power MOSFET

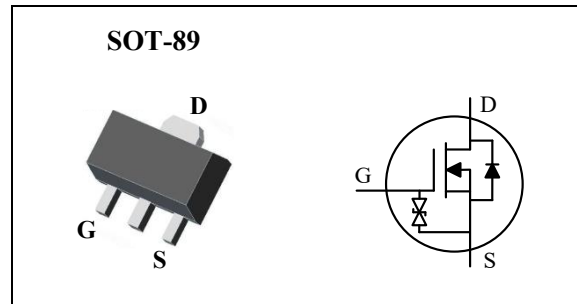
General Features

- ESD Improved Capability
- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	$R_{DS(on)(Max.)}$	$I_{DSS}(Min.)$
150V	15Ω	200mA

Applications

- New Energy Vehicles
- Industrial Automation
- Surge Protection
- Non-isolated Linear Power Supply
- Normally-on Switches
- Linear Amplifier
- Constant Current Source
- Telecom



Ordering Information

Part Number	Package	Marking	Remark
DMX1520E	SOT-89	1520	Halogen Free

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	DMX1520E	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	150	V
V_{DGX}	Drain-to-Gate Voltage ^[1]	150	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current ^[3]	0.2	A
I_{DM}	Pulsed Drain Current ^[4]	0.6	A
P_D	Power Dissipation ^[5]	1.0	W
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C

Caution: Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	DMX1520E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	125	°C/W

Electrical Characteristics

OFF Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS} = -10\text{V}$, $I_D = 250\mu\text{A}$
$I_{D(off)}$	Drain-to-Source Leakage Current	--	--	10	μA	$V_{DS} = 150\text{V}$, $V_{GS} = -10\text{V}$ $T_J = 25^\circ\text{C}$
		--	--	1	mA	$V_{DS} = 150\text{V}$, $V_{GS} = -10\text{V}$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	μA	$V_{GS} = 20\text{V}$, $V_{DS} = 0\text{V}$
		--	--	-20		$V_{GS} = -20\text{V}$, $V_{DS} = 0\text{V}$

ON Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	200	--	--	mA	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	--	10	15	Ω	$V_{GS} = 0\text{V}$, $I_D = 100\text{mA}$ [6]
$V_{GS(off)}$	Gate-to-Source Cut-off Voltage	-5.5	--	-3.5	V	$V_{DS} = 3\text{V}$, $I_D = 8\mu\text{A}$
gfs	Forward Transconductance	--	0.24	--	S	$V_{DS} = 10\text{V}$, $I_D = 100\text{mA}$

Dynamic Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	12.8	--	pF	$V_{GS} = -10\text{V}$, $V_{DS} = 25\text{V}$, $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	--	5.4	--		
C_{rss}	Reverse Transfer Capacitance	--	3.3	--		
Q_g	Total Gate Charge	--	3	--	nC	$V_{GS} = -10$ to 0V , $V_{DS} = 75\text{V}$, $I_D = 200\text{mA}$
Q_{gs}	Gate-to-Source Charge	--	0.23	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	1.1	--		

Resistive Switching Characteristics

 $T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(on)}$	Turn-on Delay Time	--	7	--	ns	$V_{GS} = -10$ to 0V , $V_{DD} = 75\text{V}$, $I_D = 200\text{mA}$, $R_G = 20\Omega$
t_r	Rise Time	--	16	--		
$t_{d(off)}$	Turn-off Delay Time	--	25	--		
t_f	Fall Time	--	120	--		

Source-Drain Diode Characteristics
 $T_A = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_{SD} = 200\text{mA}$, $V_{GS} = -10\text{V}$

NOTE:

[1] $T_J = +25^{\circ}\text{C}$ to $+150^{\circ}\text{C}$.

[2] The test is based on JEDEC EIA/JESD22-A114(HBM).

[3] $T_C = +25^{\circ}\text{C}$.

[4] Repetitive rating, pulse width limited by maximum junction temperature.

[5] $T_C = +25^{\circ}\text{C}$.

[6] Pulse width $\leq 380\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Characteristics

Figure 1. Maximum Power Dissipation vs. Case Temperature

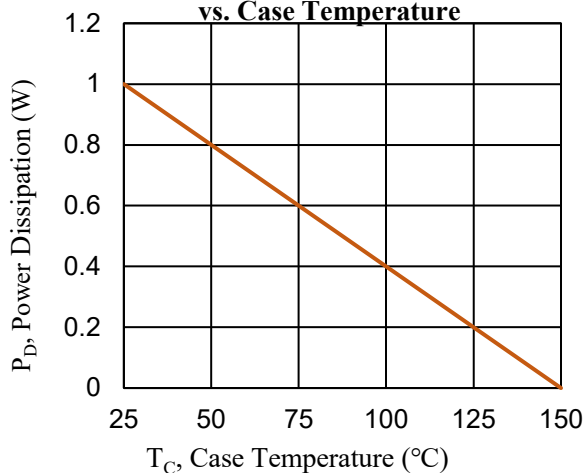


Figure 2. Maximum Continuous Drain Current vs. Case Temperature

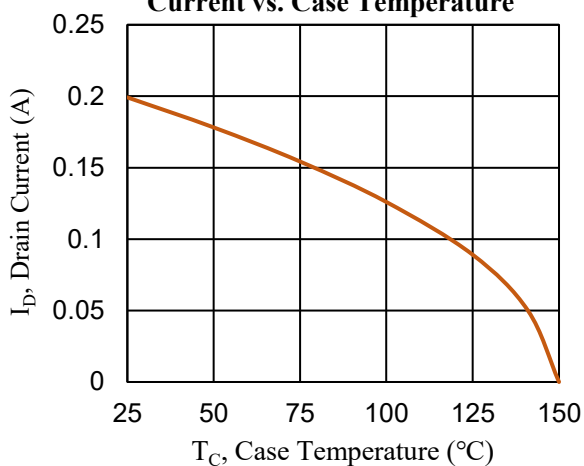


Figure 3. Typical Output Characteristics

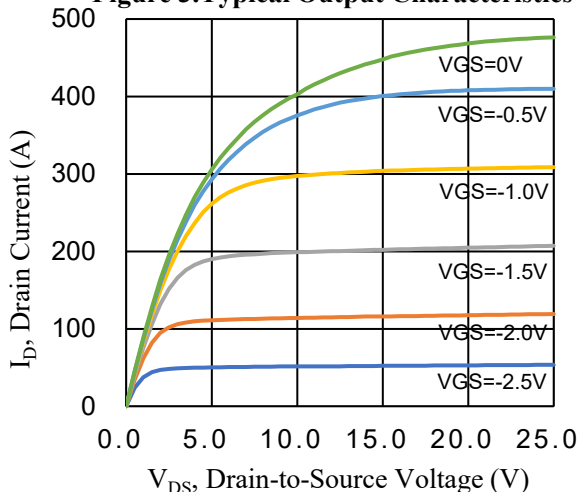


Figure 4. Typical Transfer Characteristics

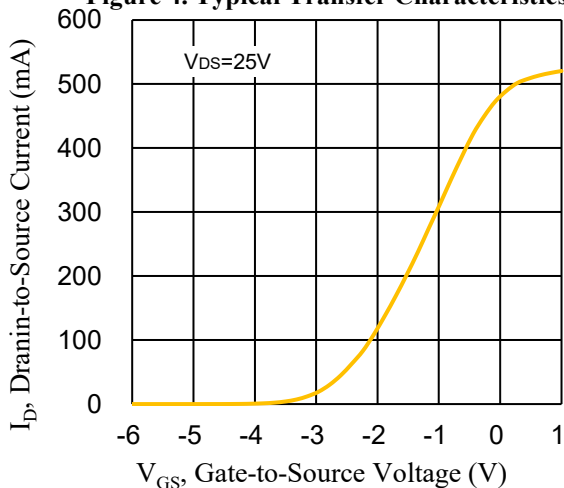


Figure 5. Maximum Rated Safe

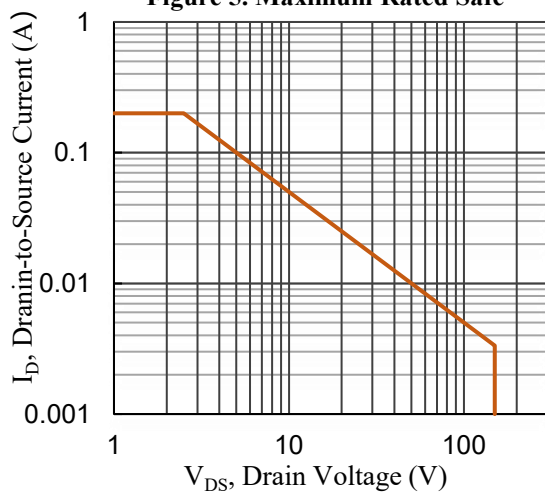
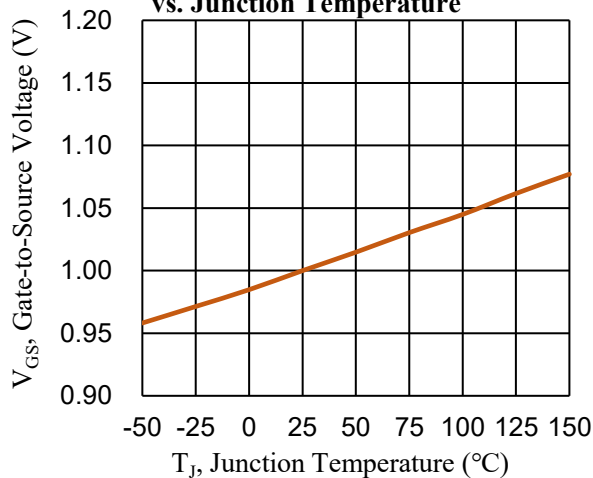


Figure 6. Typical Gate-to-Source Cut-off Voltage vs. Junction Temperature



Typical Application

In the application circuits of industrial automation, automotive electronics, and new energy, DMX1520E can be used to power LDO. As shown in Figure 7, only one DMX1520E is used in the circuit, which can convert the high input voltage into a stable low voltage to supply power to the LDO, and at the same time provide transient surge suppression for the LDO. The input voltage and output voltage of the LDO satisfy the relationship: $V_S = V_{out} + |V_{GS(OFF)}|$. The circuit has a fast response speed, a simple structure, and can effectively save costs.

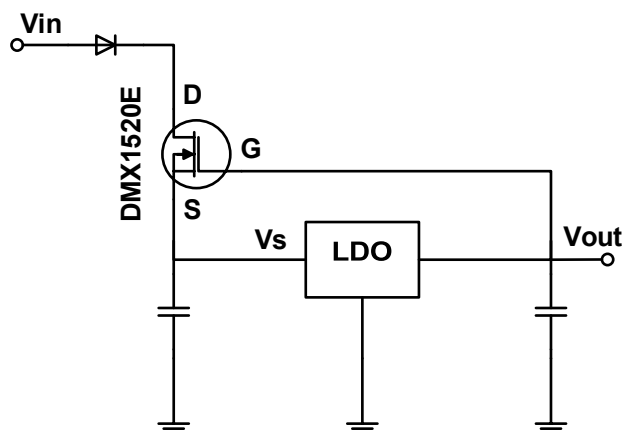


Figure 7. The Circuit of DMX1520E to power supply for LDO

Using the sub-threshold characteristics of the DMX1520E, it can form a stable current source with the resistor R. Its basic application is shown in Figure 8:

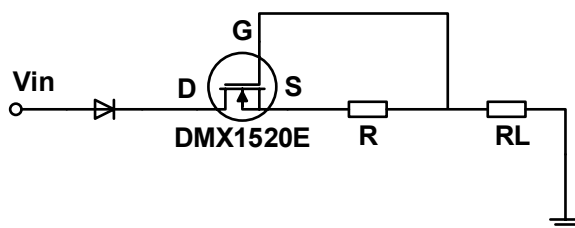
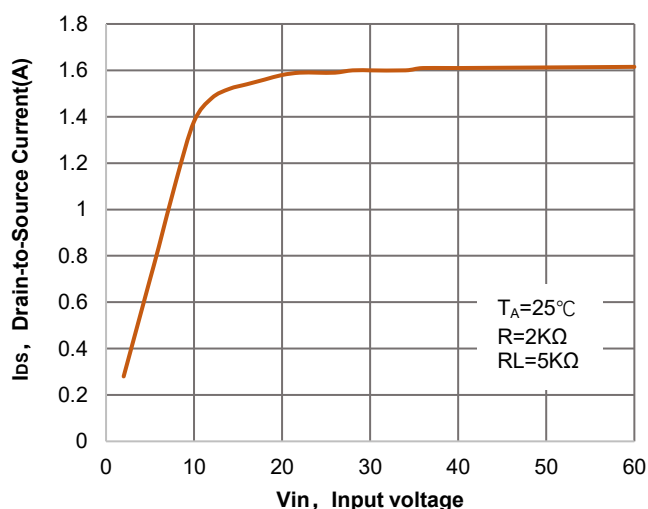


Figure 8. The Circuit of DMX1520E and resistor form constant current source

Using the sample with $V_{GS(OFF)} = -4.3V$ (@ $V_{DS} = 3V$, $I_{DS} = 8\mu A$) to test according to the circuit shown in Figure 8, the result is shown in Figure 9:

Figure 9. Typical Drain-to-Source Current vs. Input voltage



In the Type-C/PD charger circuit, DMX1520E and resistor R form a constant current source, which supplies stable power to InnoSwitch. The structure of the circuit is simple, and the DMX1520E can also provide transient surge suppression for InnoSwitch. The circuit is shown in Figure 10:

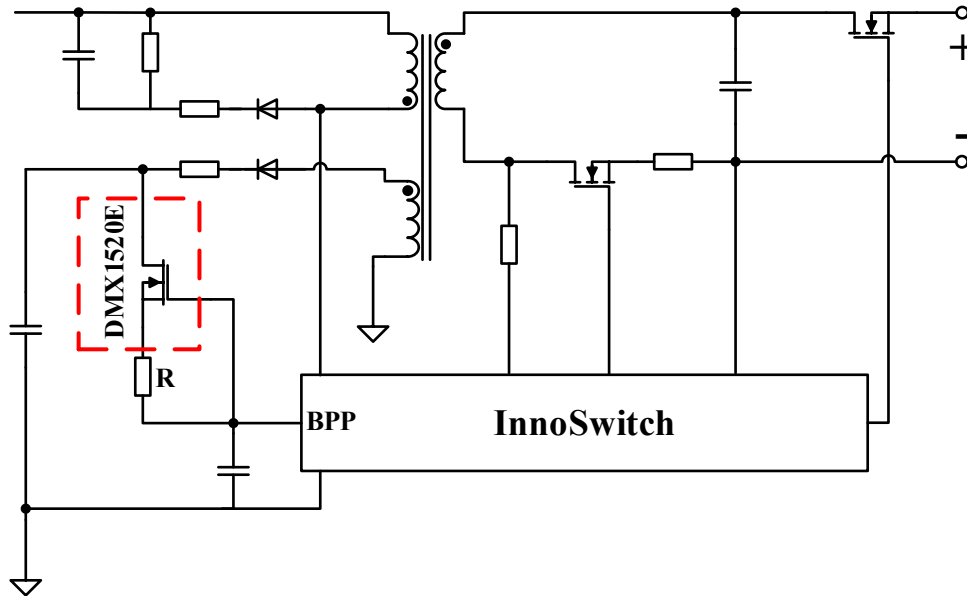
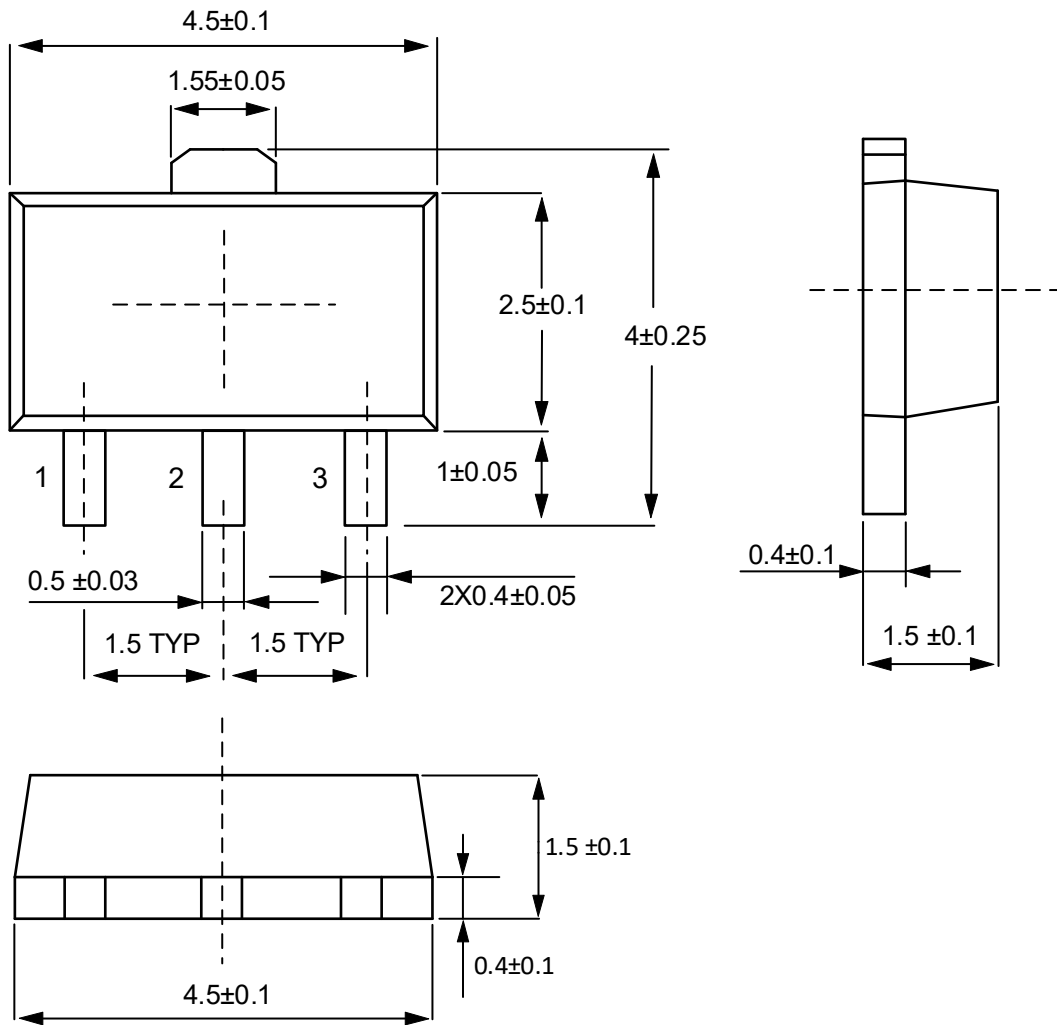


Figure 10. Constant current source circuit with DMX1520E

Package Dimensions

SOT-89



Unit: mm

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